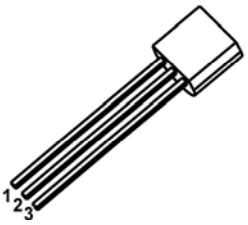
TO-92 Plastic-Encapsulate Transistors

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



S8550 TRANSISTOR (PNP)

FEATURE

- Excellent h_{FE} Linearity

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Dissipation	625	mW
T_J	Junction Temperature	150	℃
T_{stg}	Junction and Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100uA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100uA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0			-0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= - 3V, I_C=0			-0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -50mA	85		400	
	$h_{FE(2)}$	V_{CE}= -1V, IC= -500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}=- 6V, I_C=-20mA, f =30MHz	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

C	D	
120 200	200 300	300/400

Typical Characteristics